

High power cycling capability
 Low on-state and switching losses
 Optimized for line frequency rectifiers
 Designed for traction and industrial applications

Rectifier Diode Type D133-1000-18

Average forward current				I_{FAV}		1000 A		
Repetitive peak reverse voltage				V_{RRM}		1000 ÷ 1800 V		
V_{RRM}, V	1000	1100	1200	1300	1400	1500	1600	1800
Voltage code	10	11	12	13	14	15	16	18
$T_j, °C$	-60 ÷ 190							

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{FAV}	Average forward current	A	1000 1155	$T_c=117 °C$; Double side cooled; $T_c=100 °C$; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FRMS}	RMS forward current	A	1570	$T_c=117 °C$; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FSM}	Surge forward current	kA	15.0 17.0	$T_j=T_{j max}$ $T_j=25 °C$	180° half-sine wave; $t_p=10 ms$; single pulse; $V_R=0 V$;
			16.0 19.0	$T_j=T_{j max}$ $T_j=25 °C$	180° half-sine wave; $t_p=8.3 ms$; single pulse; $V_R=0 V$;
I^2t	Safety factor	$A^2s \cdot 10^3$	1100 1400	$T_j=T_{j max}$ $T_j=25 °C$	180° half-sine wave; $t_p=10 ms$; single pulse; $V_R=0 V$;
			1000 1400	$T_j=T_{j max}$ $T_j=25 °C$	180° half-sine wave; $t_p=8.3 ms$; single pulse; $V_R=0 V$;
BLOCKING					
V_{RRM}	Repetitive peak reverse voltages	V	1000 ÷ 1800	$T_{j min} < T_j < T_{j max}$; 180° half-sine wave; 50 Hz;	
V_{RSM}	Non-repetitive peak reverse voltages	V	1100 ÷ 1900	$T_{j min} < T_j < T_{j max}$; 180° half-sine wave; single pulse;	
V_R	Reverse continuous voltages	V	$0.6 \cdot V_{RRM}$	$T_j=T_{j max}$;	
THERMAL					
T_{stg}	Storage temperature	°C	-60 ÷ 50		
T_j	Operating junction temperature	°C	-60 ÷ 190		
MECHANICAL					
F	Mounting force	kN	9.0 ÷ 11.0		
a	Acceleration	m/s^2	50	Device clamped	

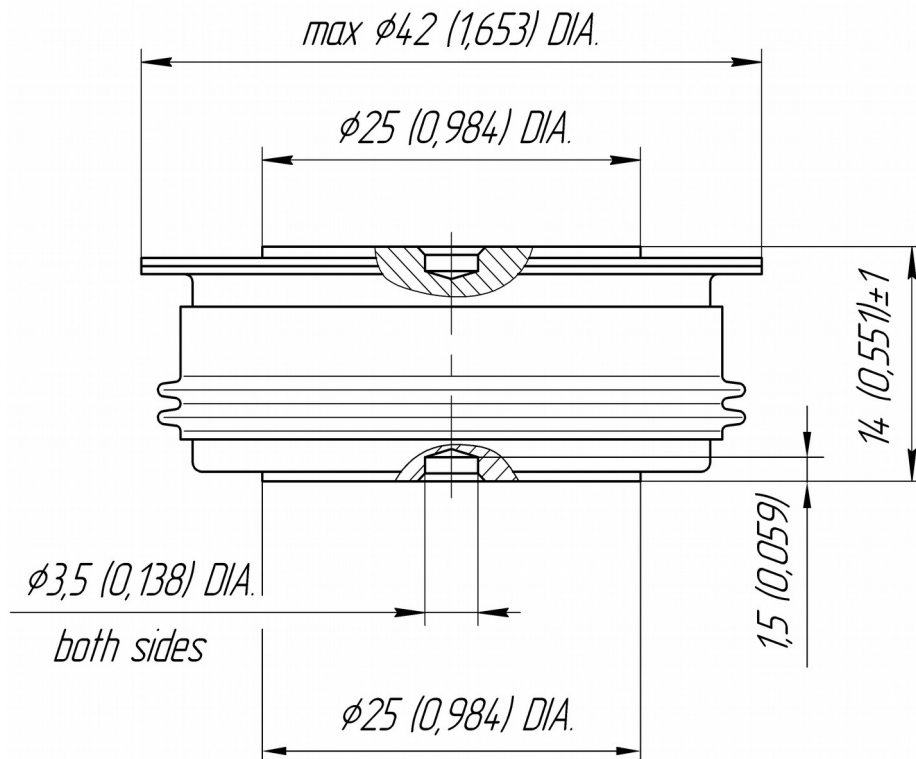
CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V_{FM}	Peak forward voltage, max	V	1.6	$T_j=25\text{ }^\circ\text{C}; I_{FM}=3140\text{ A}$
$V_{F(TO)}$	Forward threshold voltage, max	V	0.95	$T_j=T_{j\text{ max}};$
r_T	Forward slope resistance, max	m Ω	0.350	$0.5\pi I_{FAV} < I_T < 1.5\pi I_{FAV}$
BLOCKING				
I_{RRM}	Repetitive peak reverse current, max	mA	50	$T_j=T_{j\text{ max}};$ $V_R=V_{RRM}$
SWITCHING				
Q_{rr}	Total recovered charge, max	μC	1250	$T_j=150\text{ }^\circ\text{C}; I_{TM}=400\text{ A};$
t_{rr}	Reverse recovery time, max	μs	19	$di_R/dt=-10\text{ A}/\mu\text{s};$
I_{rrM}	Peak reverse recovery current, max	A	132	$V_R=100\text{ V}$
THERMAL				
R_{thjc}	Thermal resistance, junction to case, max	$^\circ\text{C}/\text{W}$	0.040	Double side cooled
R_{thjc-A}			0.088	Anode side cooled
R_{thjc-K}			0.072	Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	$^\circ\text{C}/\text{W}$	0.009	Direct current
MECHANICAL				
w	Weight, typ	g	110	
D_s	Surface creepage distance	mm (inch)	11.10 (0.437)	
D_a	Air strike distance	mm (inch)	11.60 (0.457)	

PART NUMBERING GUIDE

D	133	1000	18	N
1	2	3	4	5

1. D — Rectifier Diode
2. Design version
3. Average forward current, A
4. Voltage code
5. Ambient conditions: N – normal; T – tropical



All dimensions in millimeters (inches)

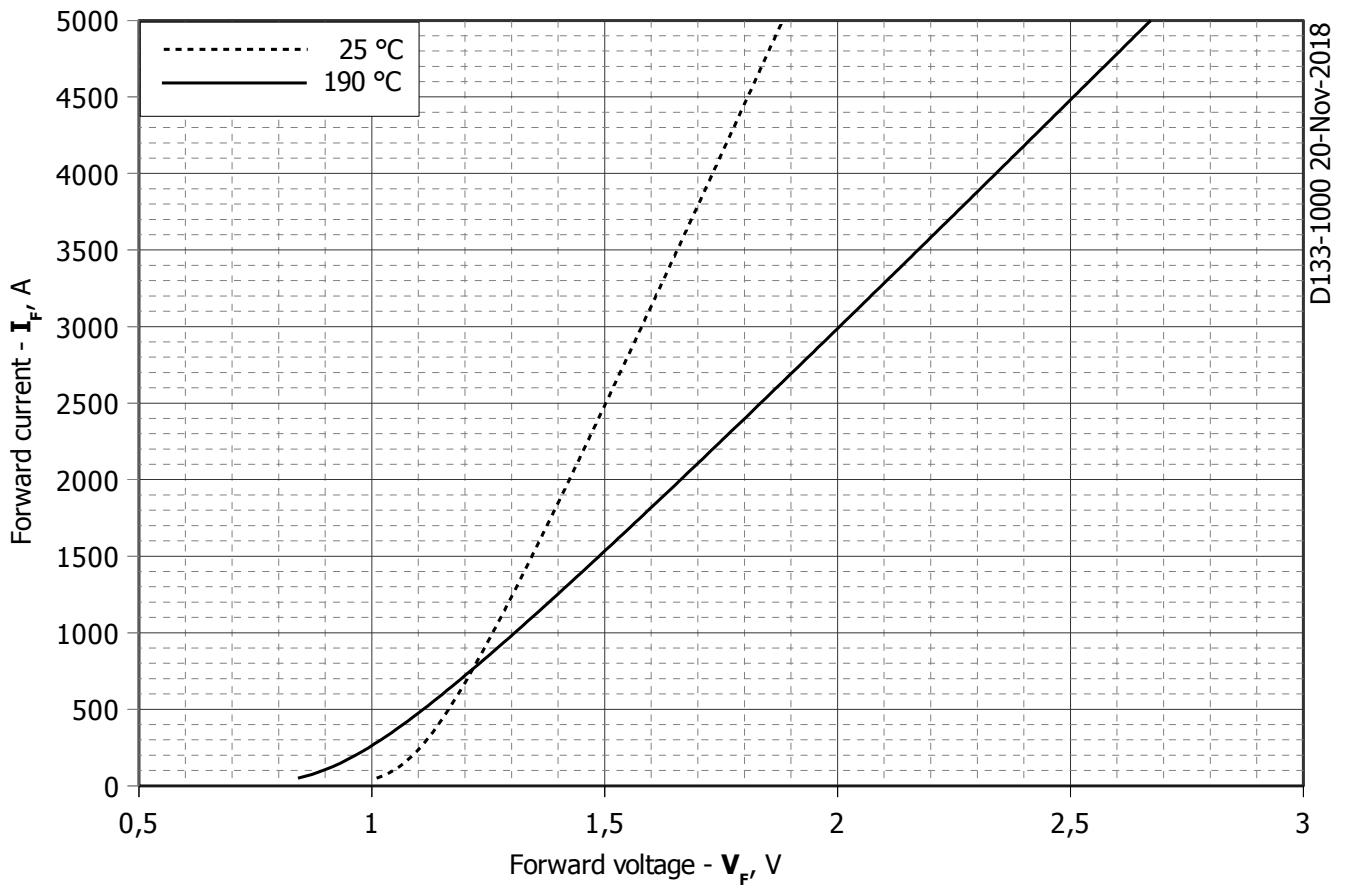


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j\text{max}}$
A	0,82474000	0,60122000
B	0,00015147	0,00032413
C	0,04814600	0,05817400
D	-0,00155470	-0,00063830

Forward characteristic model (see Fig. 1).

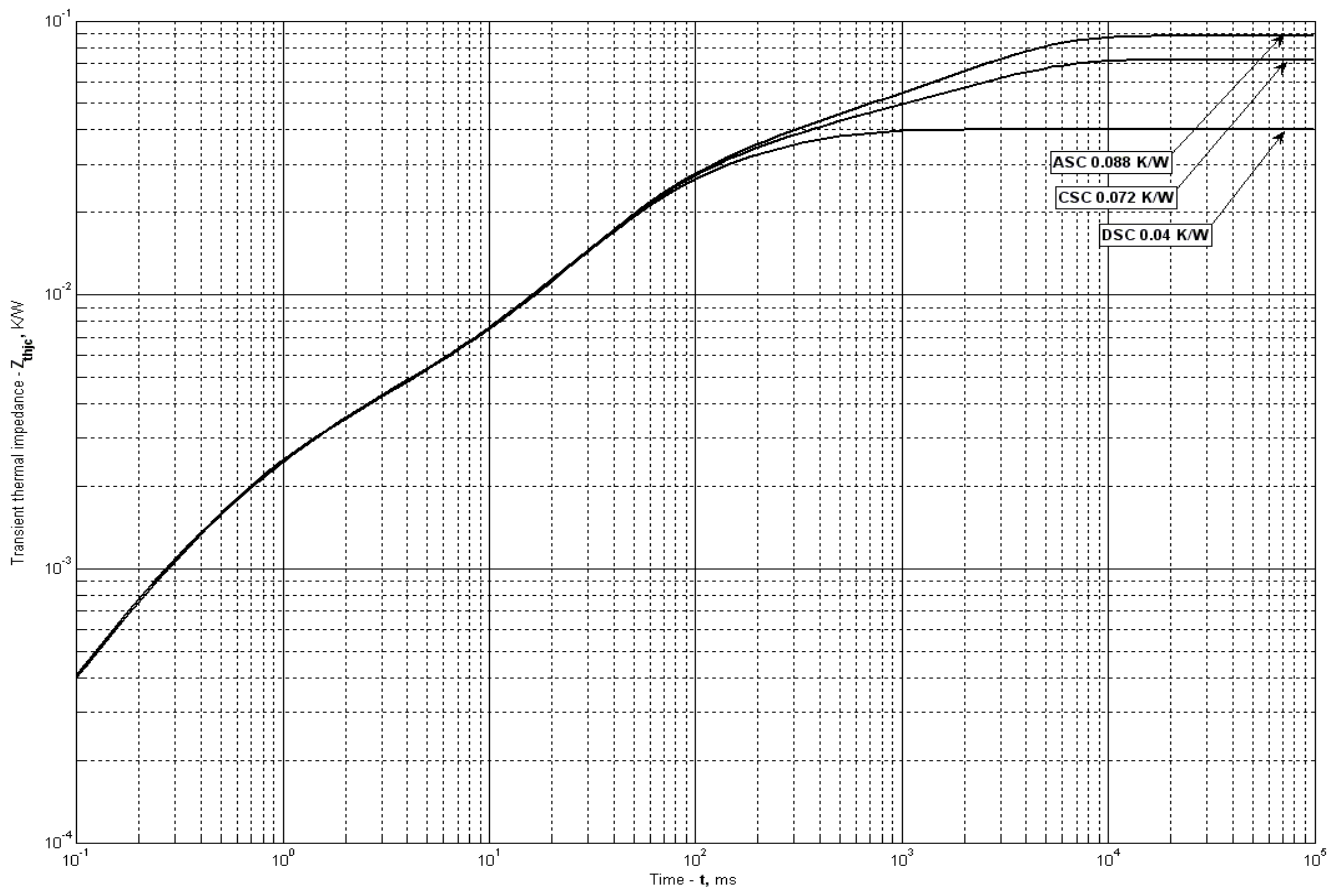


Fig 2 – Transient thermal impedance

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i , K/W	0.01423	0.01906	0.003576	0.002535	-4.666e-005	0.0006479
τ_i , s	0.265	0.05901	0.03499	0.001252	0.000001	0.0002488

DC Anode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.04804	0.001789	0.01342	0.02147	0.001374	0.001945
τ_i , s	2.651	0.4195	0.2622	0.05451	0.002585	0.0005847

DC Cathode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.03216	0.01306	0.002934	0.02064	0.001493	0.001786
τ_i , s	2.647	0.2831	0.1455	0.05284	0.002255	0.0005519

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

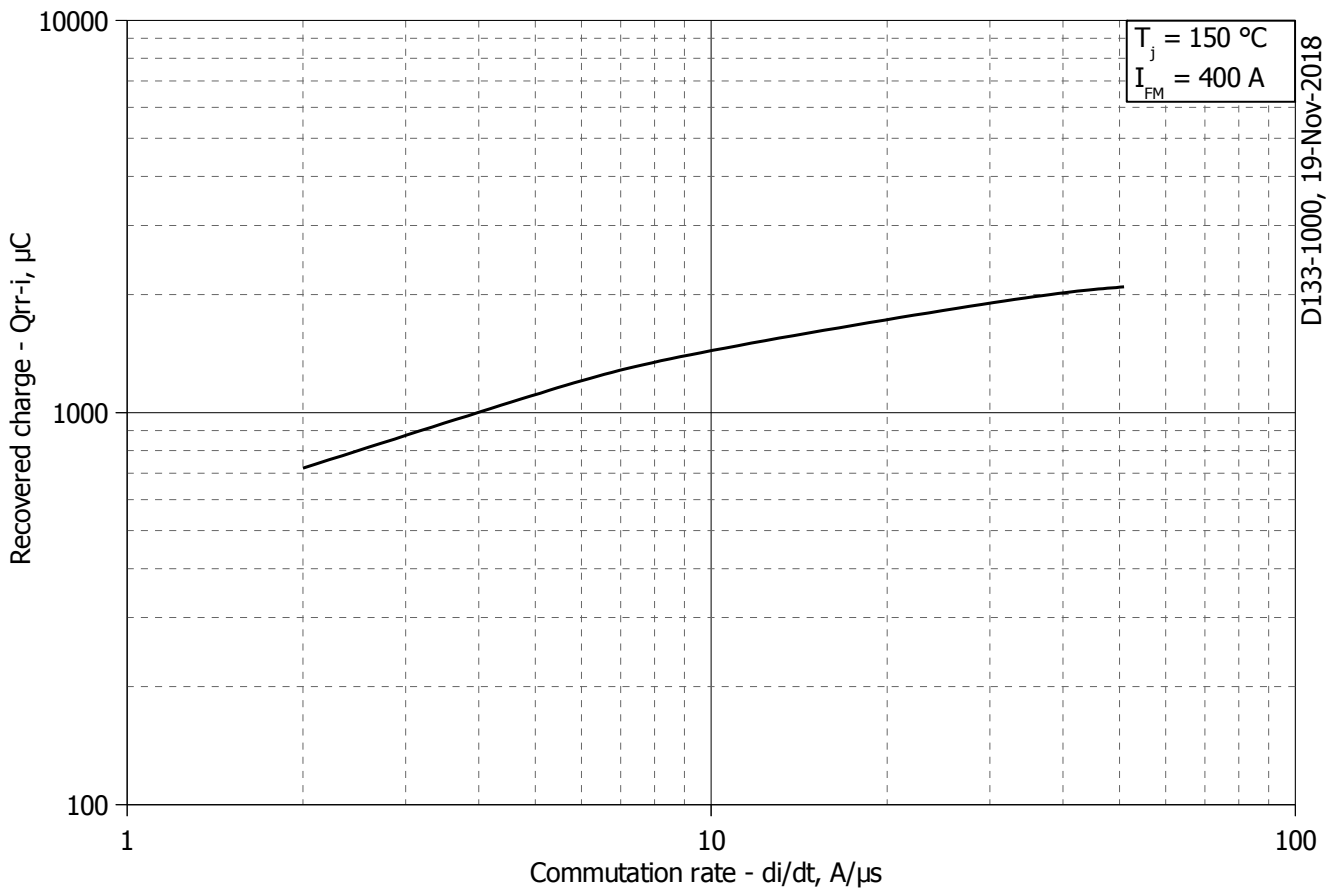


Fig 3 – Total recovered charge, Q_{rr-i} (integral)

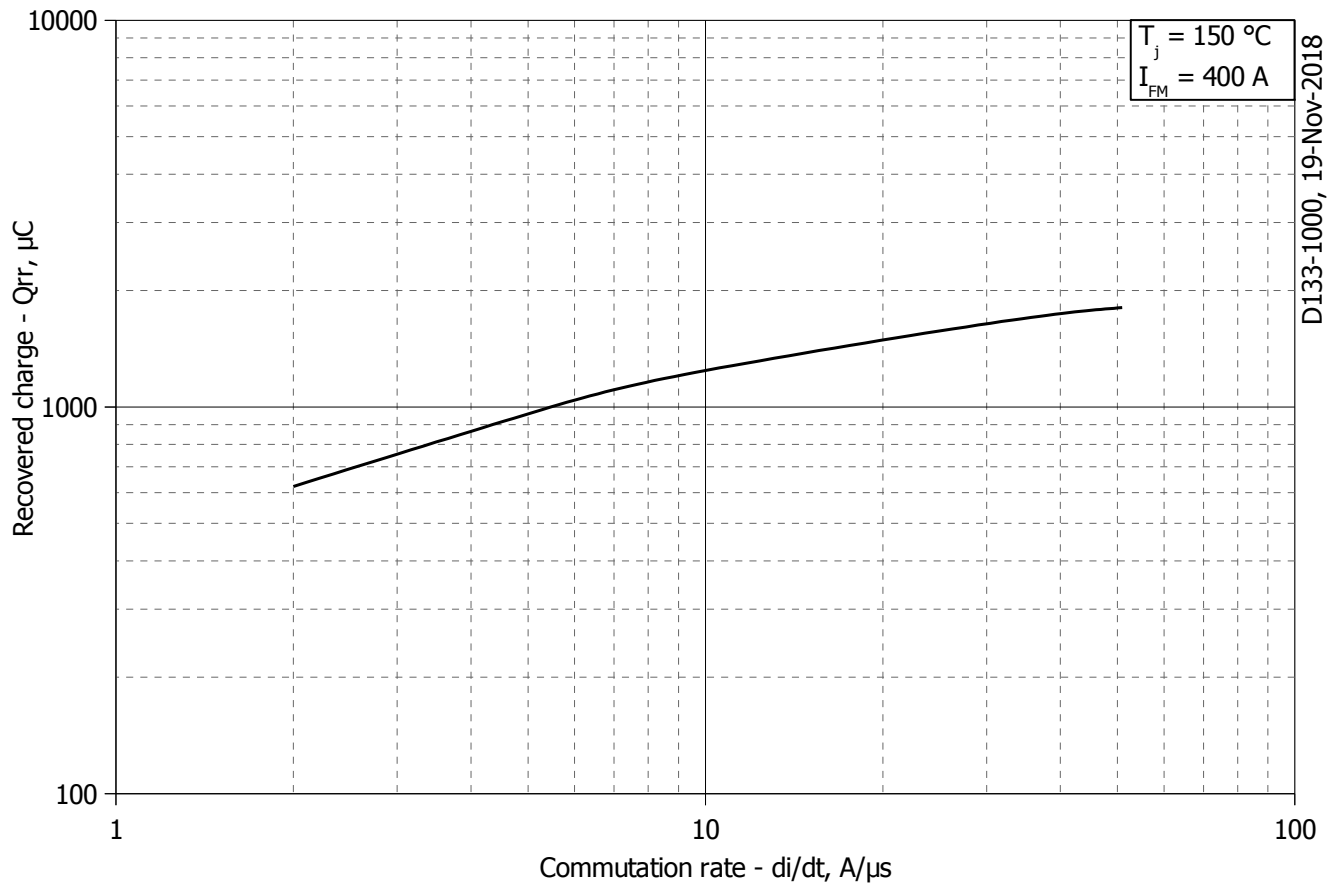
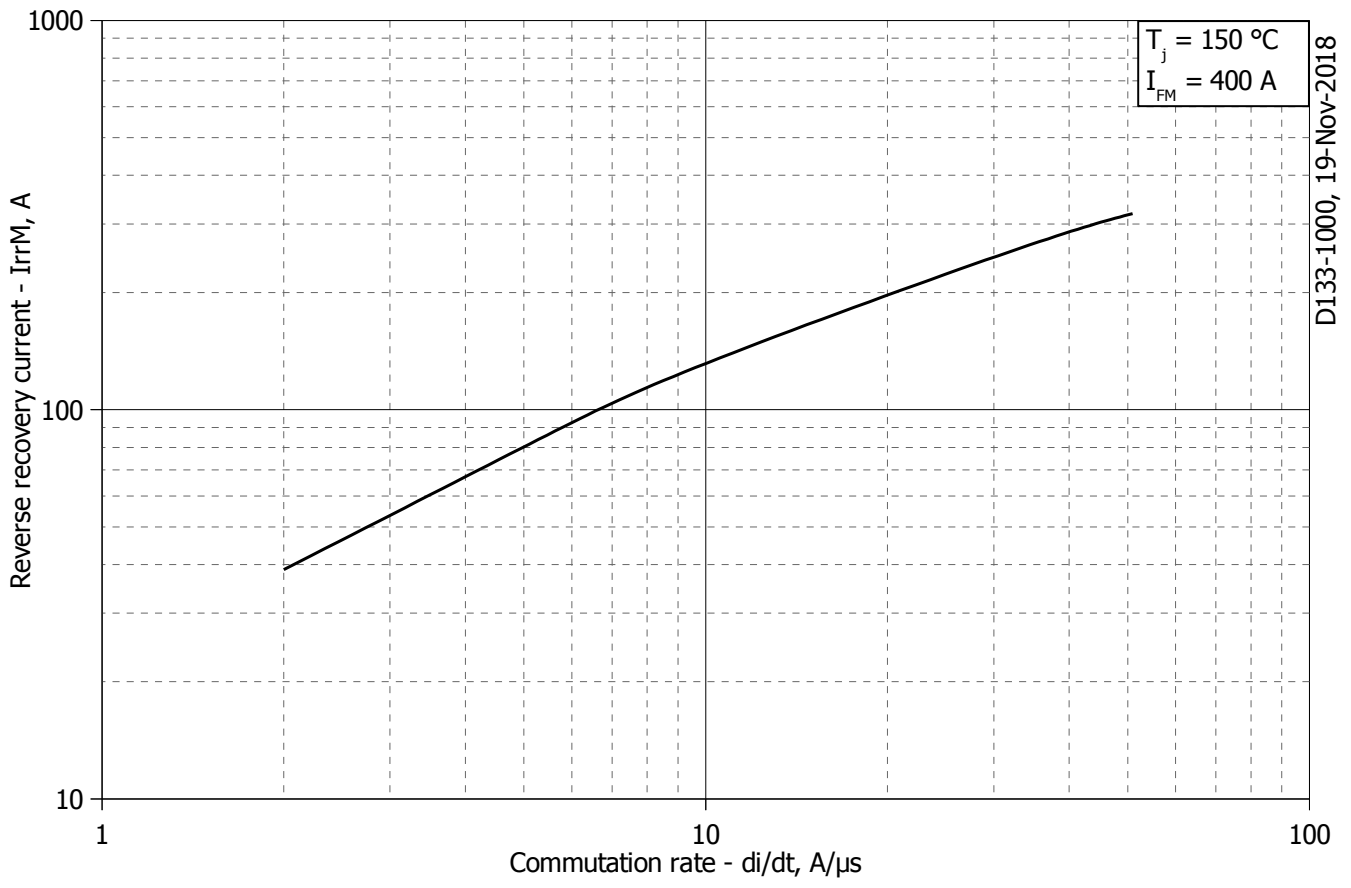
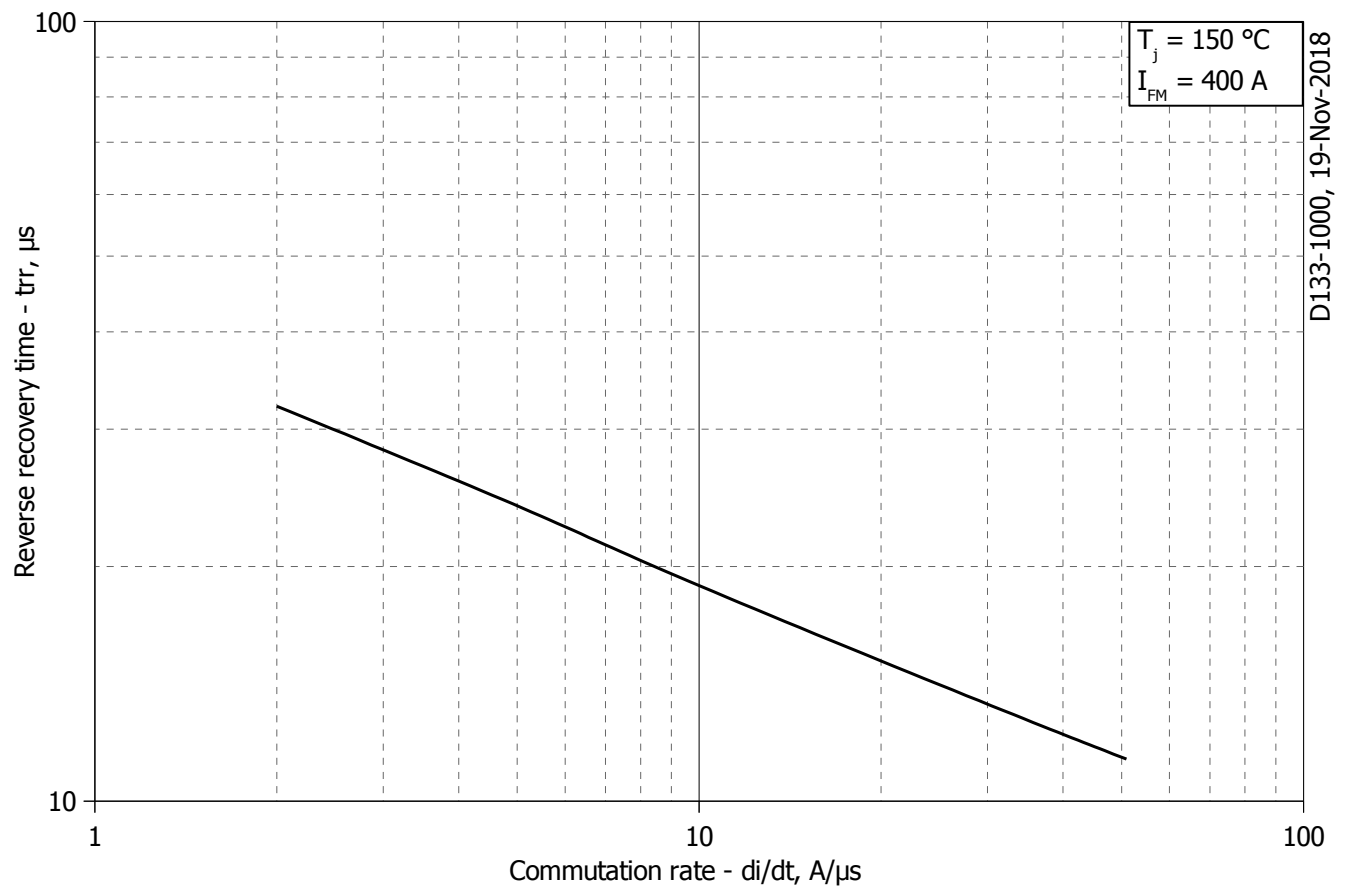


Fig 4 - Recovered charge, Q_{rr} (25% chord)



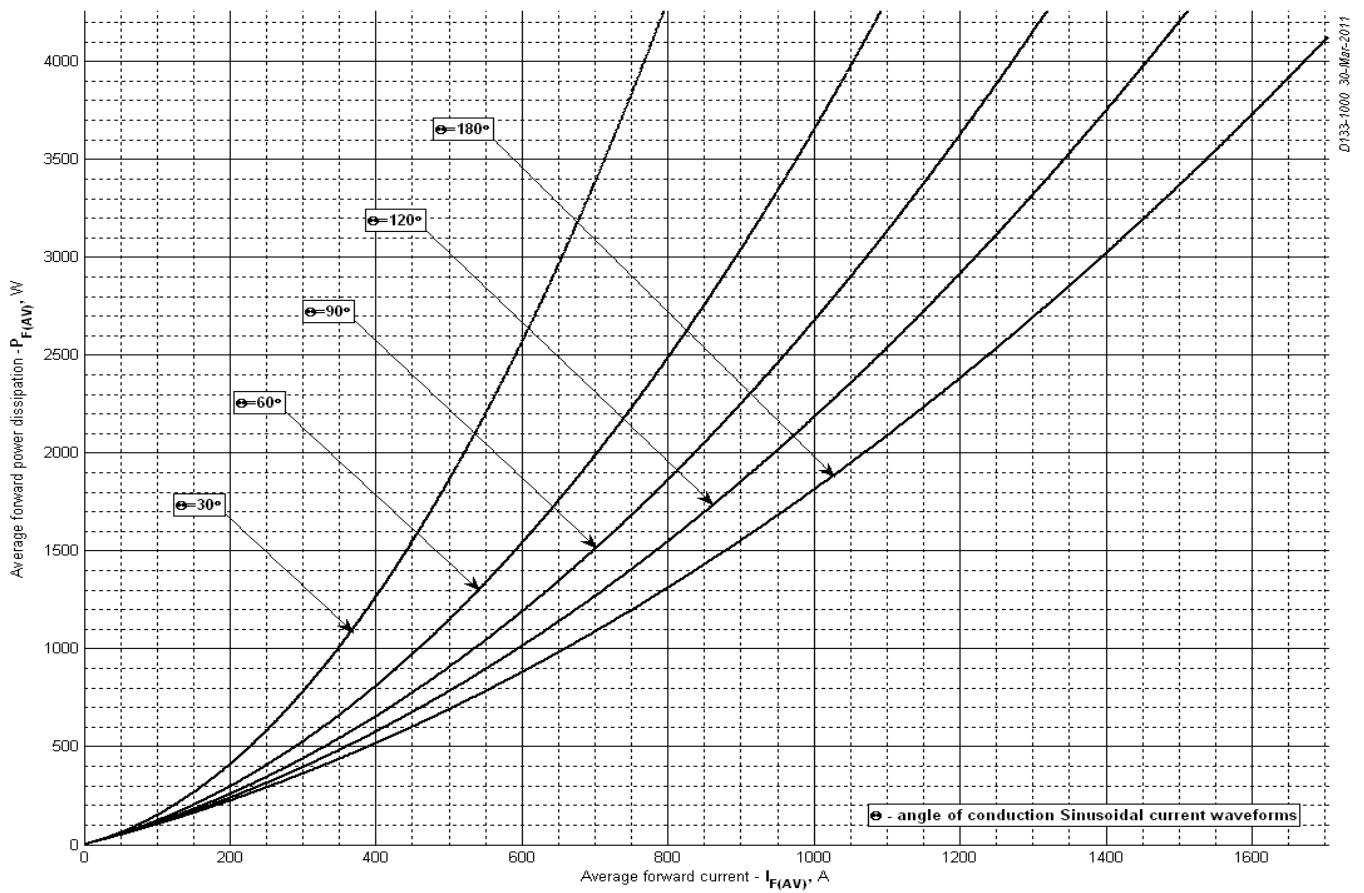
D133-1000, 19-Nov-2018

Fig 5 – Peak reverse recovery current, I_{rrM}



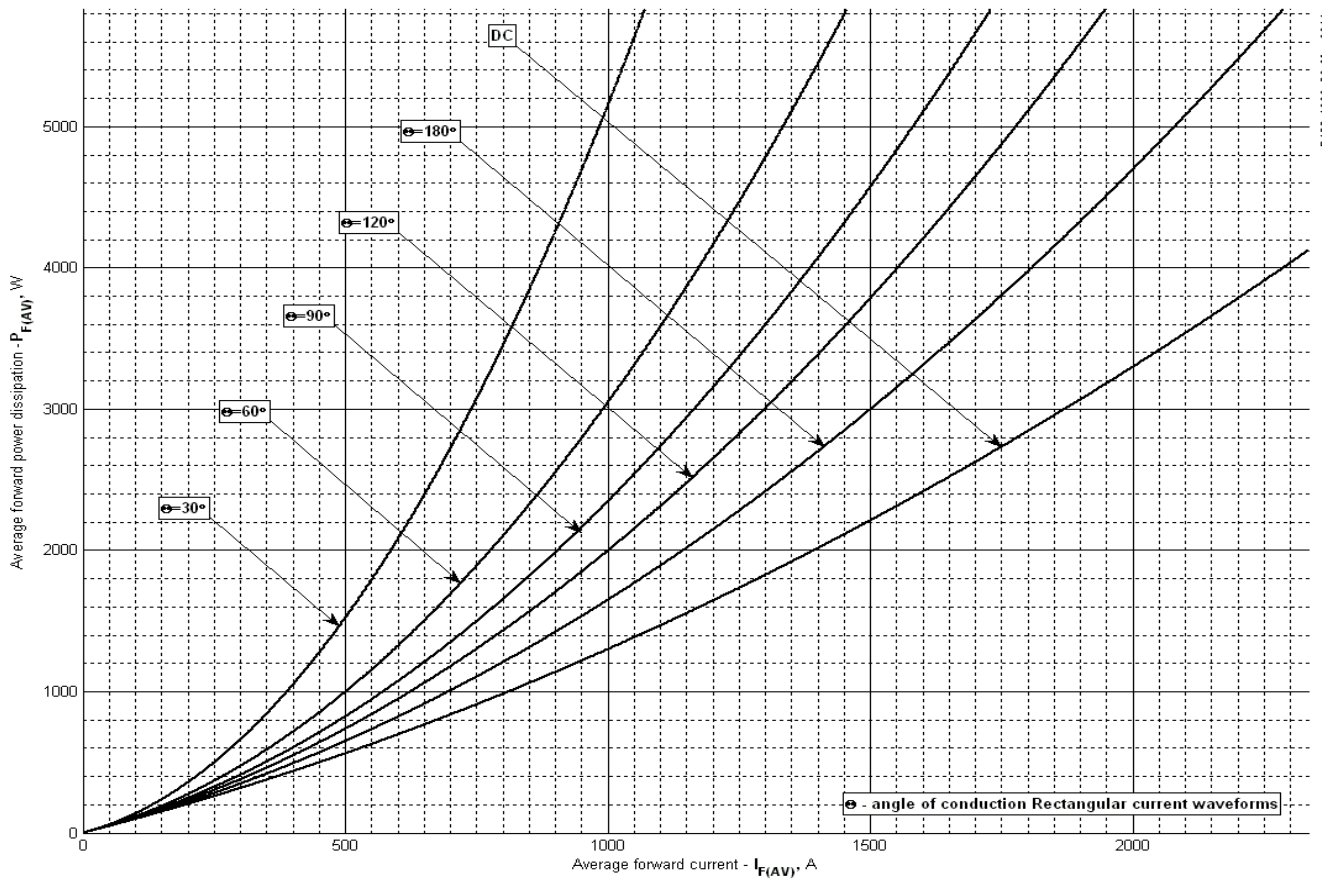
D133-1000, 19-Nov-2018

Fig 6 – Maximum recovery time, t_{rr} (25% chord)



D133-1000 30-Mar-2011

Fig 7 - Mean forward power dissipation P_{FAV} vs. Mean forward current I_{FAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)



D133-1000 30-Mar-2011

Fig 8 - Mean forward power dissipation P_{FAV} vs. Mean forward current I_{FAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

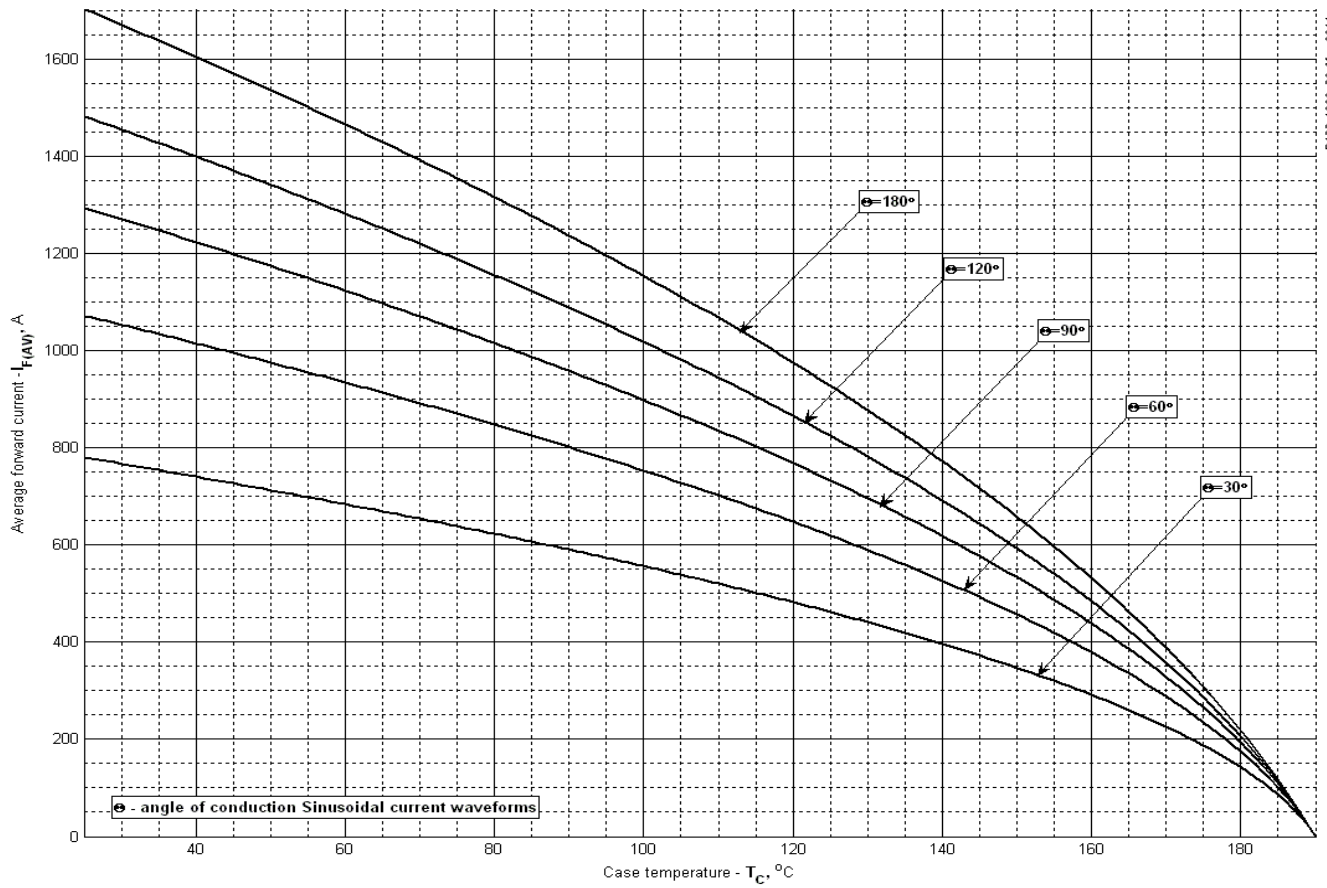


Fig 9 – Mean forward current I_{FAV} vs. Case temperature T_C for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

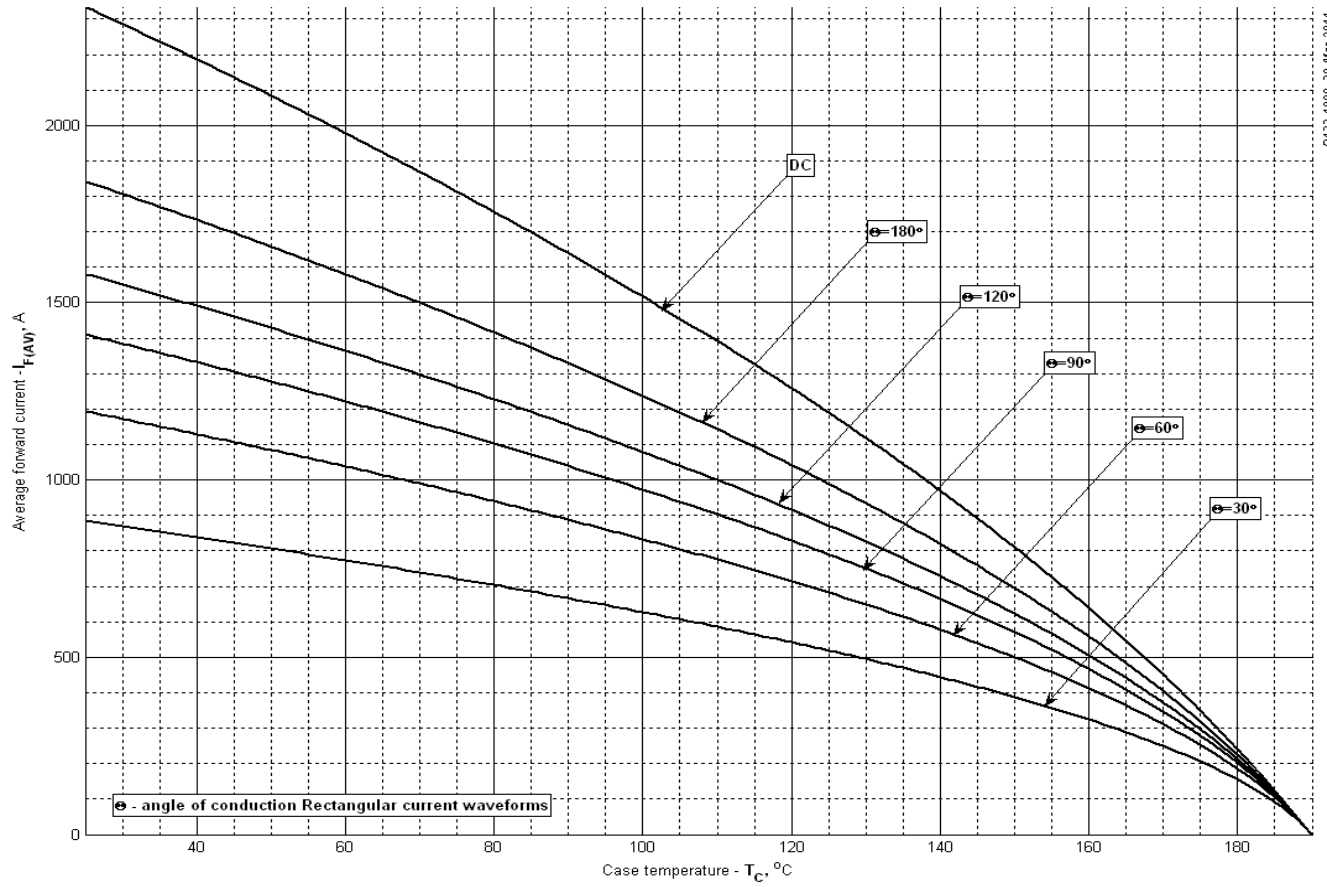


Fig 10 - Mean forward current I_{FAV} vs. Case temperature T_C for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

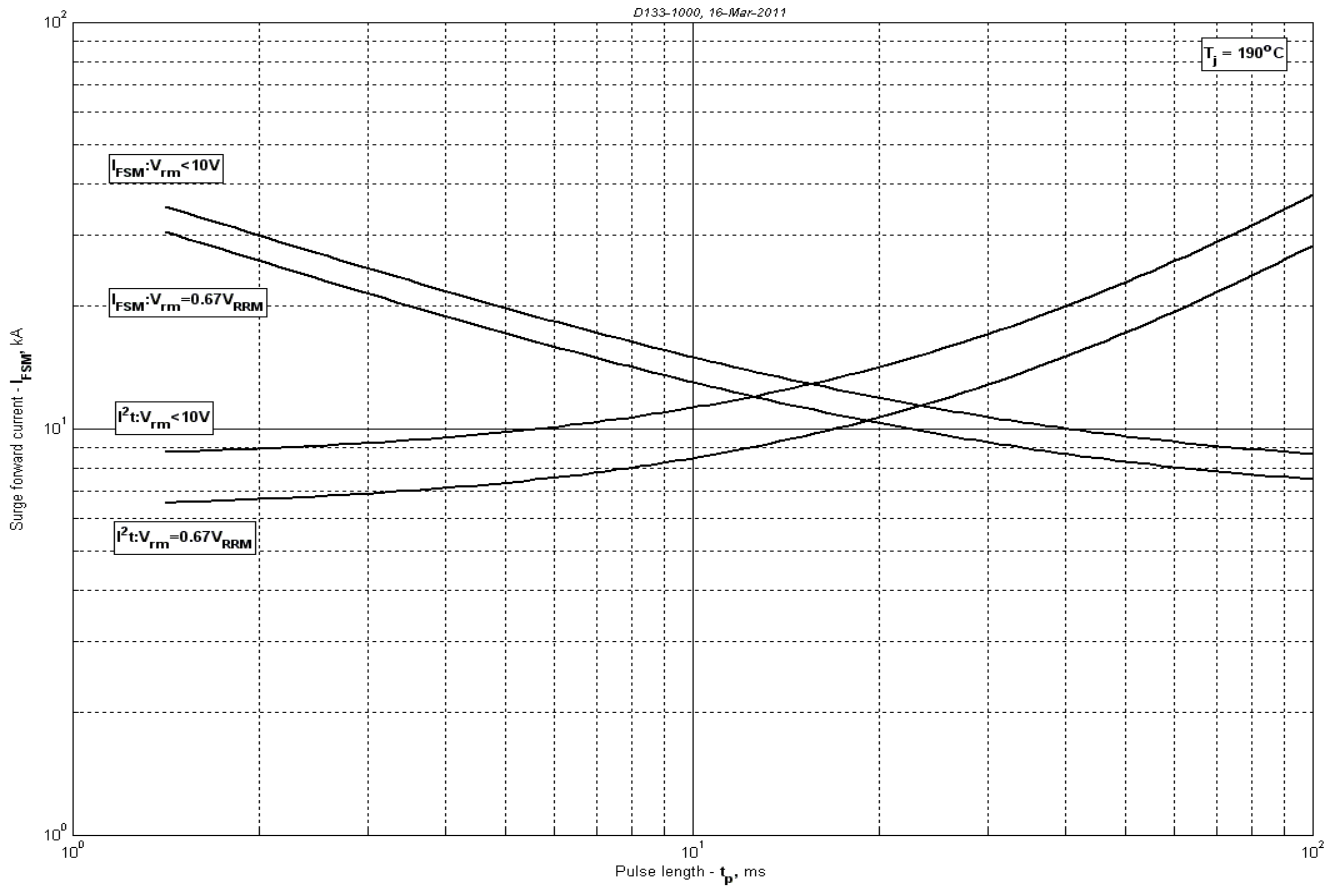


Fig 11 – Maximum surge and I^2t ratings

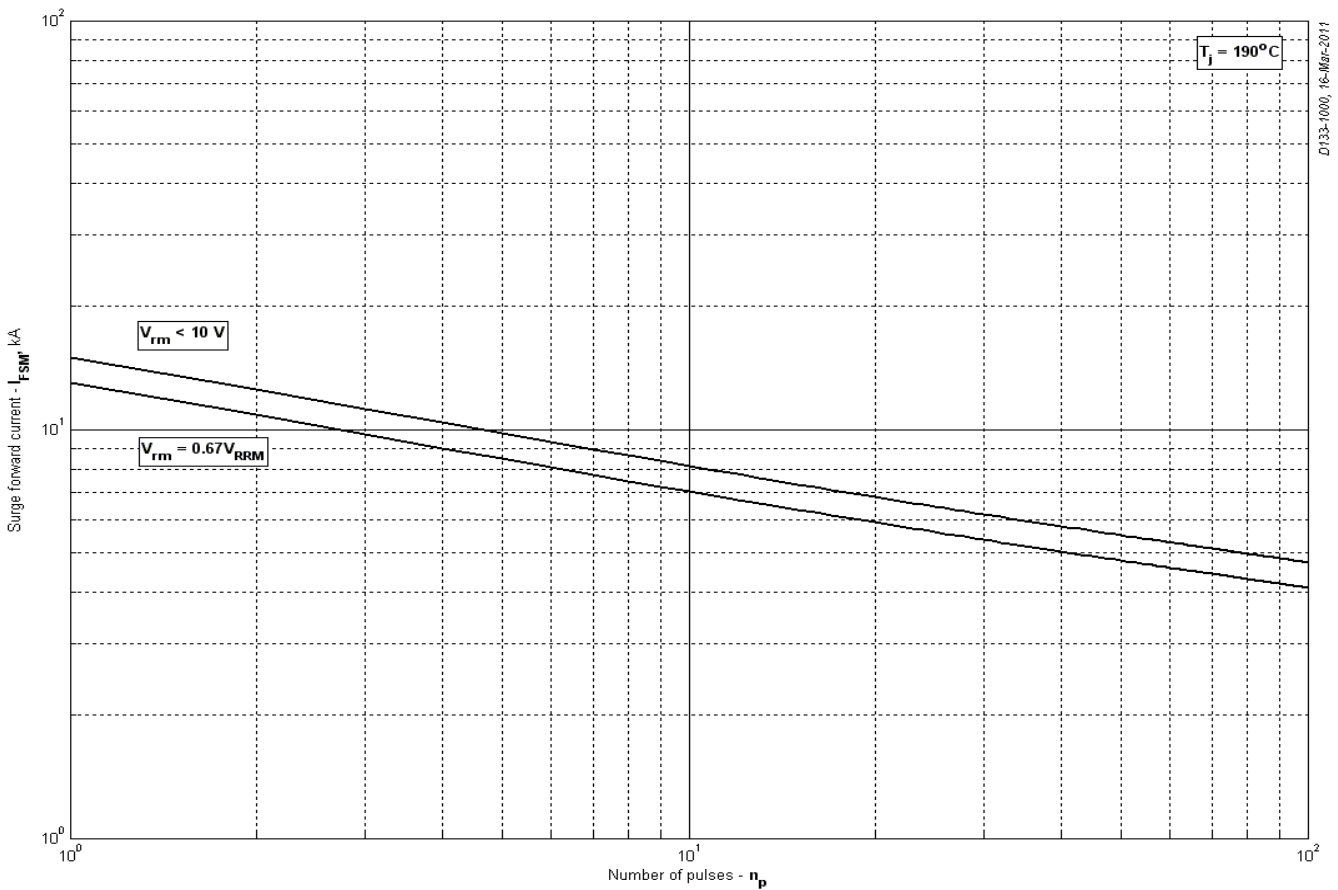


Fig 12 - Maximum surge ratings